LONGITUDINAL MAGNETORESISTANCE OF UNIAXIALLY DEFORMED p-SILICON AT $\mathbf{J} \parallel \mathbf{B} \parallel [001]$

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S u m m a r y

The influence of uniaxial pressure on the longitudinal magnetoresistance of pure p-Si crystals at the temperature $T = 77.4$ K and in the magnetic field $B = 45$ T has been studied. The results are discussed making allowance for negative effective masses of holes. A reduction of magnetoresistance with increase in the external pressure confirms the reduction of effective hole masses.